## TIP131, TIP132 (NPN), TIP137 (PNP)

### **Darlington Complementary Silicon Power Transistors**

Designed for general-purpose amplifier and low-speed switching applications.

### Features

- High DC Current Gain  $h_{FE} = 2500 (Typ) @ I_C$ 
  - = 4.0 Adc
- Collector-Emitter Sustaining Voltage @ 30 mAdc
   V<sub>CEO(sus)</sub> = 80 Vdc (Min) TIP131
   = 100 Vdc (Min) TIP132, TIP137
- Low Collector–Emitter Saturation Voltage
  - $V_{CE(sat)} = 2.0 \text{ Vdc} (Max) @ I_C = 4.0 \text{ Adc}$

 $= 3.0 \text{ Vdc} (\text{Max}) @ I_{\text{C}} = 6.0 \text{ Adc}$ 

- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- Pb-Free Packages are Available\*

### MAXIMUM RATINGS

Rating	Symbol	TIP131	TIP132 TIP137	Unit	
Collector-Emitter Voltage	V <sub>CEO</sub>	80	100	Vdc	
Collector-Base Voltage	-Base Voltage V <sub>CB</sub> 80				
Emitter-Base Voltage	V <sub>EB</sub>	5.	Vdc		
Collector Current – Continuous Peak	Ι <sub>C</sub>	8.0 12		Adc	
Base Current	I <sub>B</sub>	300		mAdc	
Total Power Dissipation @ $T_C = 25^{\circ}C$	PD	70		W	
Total Power Dissipation @ $T_A = 25^{\circ}C$	PD	2.0		W	
Operating and Storage Junction, Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	−65 to +150		°C	

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.78	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	63.5	°C/W

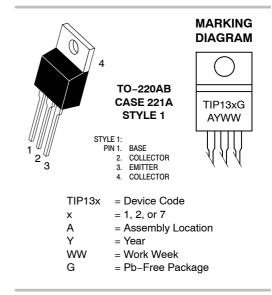
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



### **ON Semiconductor®**

http://onsemi.com

### DARLINGTON 8 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 80–100 VOLTS, 70 WATTS



### ORDERING INFORMATION

Device	Package	Shipping
TIP131	TO-220	50 Units/Rail
TIP131G	TO-220 (Pb-Free)	50 Units/Rail
TIP132	TO-220	50 Units/Rail
TIP132G	TO–220 (Pb–Free)	50 Units/Rail
TIP137	TO-220	50 Units/Rail
TIP137G	TO-220 (Pb-Free)	50 Units/Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### TIP131, TIP132 (NPN), TIP137 (PNP)

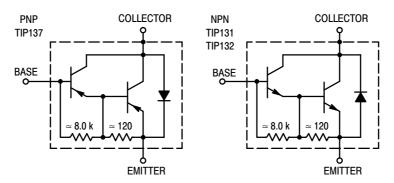


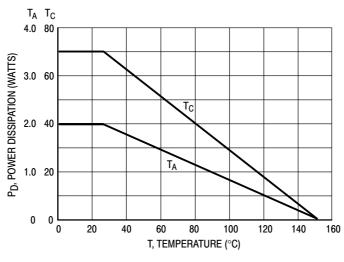
Figure 1. Darlington Circuit Schematic

### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				-	
Collector-Emitter Sustaining Voltage (Note 1) $(I_{C} = 30 \text{ mAdc}, I_{B} = 0)$	TIP131 TIP132, TIP137	V <sub>CEO(sus)</sub>	80 100		Vdc
Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}, I_B = 0$ ) ( $V_{CE} = 50 \text{ Vdc}, I_B = 0$ )	TIP131 TIP132, TIP137	I <sub>CEO</sub>		0.5 0.5	mAdc
Collector Cutoff Current ( $V_{CB} = 80 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 100 \text{ Vdc}, I_E = 0$ )	TIP131 TIP132, TIP137	I <sub>CBO</sub>		0.2 0.2	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}, I_C = 0$ )		I <sub>EBO</sub>	-	5.0	mAdc
ON CHARACTERISTICS (Note 1)				-	
DC Current Gain ( $I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$ ) ( $I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$ )		h <sub>FE</sub>	500 1000	_ 15000	-
Collector-Emitter Saturation Voltage ( $I_C = 4.0 \text{ Adc}, I_B = 16 \text{ mAdc}$ ) ( $I_C = 6.0 \text{ Adc}, I_B = 30 \text{ mAdc}$ )		V <sub>CE(sat)</sub>		2.0 3.0	Vdc
Base-Emitter On Voltage $(I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$		V <sub>BE(on)</sub>	-	2.5	Vdc

1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

### TIP131, TIP132 (NPN), TIP137 (PNP)





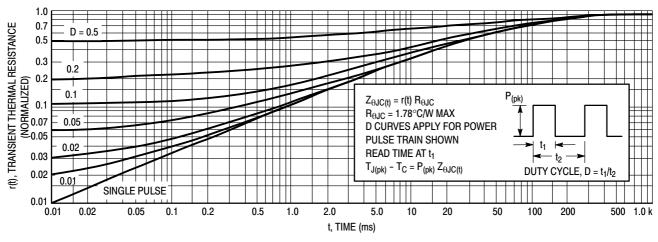


Figure 3. Thermal Response

S

# onsemi

		TO-220 CASE 221A ISSUE AK						DATE	13 JAN 2022
SCALE 1:1			1. C 2. C 3. C	CONTR DIMEN LEAD	ROLLING DI ISION Z DEI D IRREGULA	MENSION FINES A ZO ARITIES AR	ONE WHERE AL E ALLOWED.		
			4. N	лах м	VIDTHFOR	F102 DEV	ICE = 1.35MM		
			Г		INC	HES	MILLIM	ETERS	
				ым 🛛	MIN.	MAX.	MIN.	MAX.	
	2 3			A	0.570	0.620	14.48	15.75	
				в	0.380	0.415	9.66	10.53	
н —	₩₩			с	0.160	0.190	4.07	4.83	
	7 \7	H I		D	0.025	0.038	0.64	0.96	
z_				F	0.142	0.161	3.60	4.09	
<u> </u>	I K			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	Щ Щ <u> </u>	Ü I		J	0.014	0.024	0.36	0.61	
	Г <mark>і</mark>			к	0.500	0.562	12.70	14.27	
V — + I I-	►- <b>  </b> ``.			L	0.045	0.060	1.15	1.52	
G <del></del>	.  <mark> </mark> <sup></sup> J <sup>−</sup>			N	0.190	0.210	4.83	5.33	
· · · ·	- <b>→  </b> D			Q	0.100	0.120	2.54	3.04	
	N 🖛			R	0.080	0.110	2.04	2.79	
				s	0.045	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U	0.000	0.050	0.00	1.27	
				V	0.045		1.15		
				Z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2.	BASE         PIN 1.           COLLECTOR         2.           EMITTER         3.           COLLECTOR         4.           STYLE 6:         GATE           DRAIN         2.	EMITTER COLLECTOR EMITTER ANODE CATHODE	IN 1. CAT 2. ANO 3. GAT 4. ANO LE 7: IN 1. CAT 2. ANO	ode Te ode Thode ode		2. 3. 4. STYLE 8: PIN 1. 2.	MAIN TERMINAL MAIN TERMINAL GATE MAIN TERMINAL CATHODE ANODE	2	
4. STYLE 9: PIN 1.	DRAIN 4. STYLE 10 GATE PIN 1.	ANODE CATHODE GATE P SOURCE	3. CAT 4. ANO LE 11: IN 1. DR/ 2. SOU	ode Ain		4. STYLE 12: PIN 1.	EXTERNAL TRIP ANODE MAIN TERMINAL MAIN TERMINAL	. 1	
3.	EMITTER 3.	DRAIN SOURCE	3. GAT 4. SOL	ΤE		3.	GATE NOT CONNECTI		

 
 DOCUMENT NUMBER:
 98ASB42148B
 Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

 DESCRIPTION:
 TO-220
 PAGE 1 OF 1

 onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative